

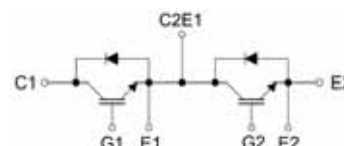
“HALF-BRIDGE” IGBT

Features

- Trench gate + field stopper, using Infineon chip design
- 10μs Short circuit capability
- Low turn-off losses
- Short tail current for over 18KHz
- Positive $V_{CE(on)}$ temperature coefficient

Applications

- AC & DC Motor controls
- VVVF inverters
- Optimized for high frequency inverter Type Welding machines
- High frequency SMPS
- UPS, Robotics

 $V_{CES} = 1200V$
 $I_c = 100A$
 $V_{CE(on)} \text{ typ.} = 1.7V$
 $@ I_c = 100A$


Package : V1

Absolute Maximum Ratings @ $T_c = 25^\circ C$ (per leg)

Symbol	Parameter	Condition	Ratings	Unit
V_{CES}	Collector-to-Emitter Voltage	$V_{GE} = 0V, I_c = 500\mu A$	1200	V
V_{GES}	Gate emitter voltage		± 20	V
I_c	Continuous Collector Current	$T_c = 80^\circ C(25^\circ C)$	100(140)	A
I_{CM}	Pulsed collector current	$T_c = 25^\circ C$	200	A
I_F	Diode Continuous Forward Current	$T_c = 80^\circ C(25^\circ C)$	100(140)	A
I_{FM}	Diode Maximum Forward Current	$TC=(25^\circ C)$	200	A
T_{SC}	Short Circuit Withstand Time		10	μs
V_{iso}	Isolation Voltage test	AC 1 minute	2500	V
T_j	Junction Temperature		-40 ~ 150	°C
T_{stg}	Storage Temperature		-40 ~ 125	°C
Weight	Weight of Module		190	g
Mounting	Power Terminal Screw : M5		3.5	Nm
Torque	Terminal connection Screw : M5		3.5	Nm

Electrical Characteristics @ $T_j = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameters	Min	Typ	Max	Unit	Test conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	-	1350	1374	V	$V_{GE} = 0V, I_C = 200\mu A$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	1.4	1.7	2.1		$I_C = 100A, V_{GE} = 15V$
$V_{GE(th)}$	Gate Threshold Voltage	4.0	5.8	6.5		$V_{CE} = V_{GE}, I_C = 250\mu A$
I_{CES}	Zero Gate Voltage Collector Current	-	-	500	μA	$V_{GE} = 0V, V_{CE} = 1200V$
I_{GES}	Gate-to-Emitter Leakage Current	-	-	± 100	nA	$V_{CE} = 0V, V_{GE} = \pm 20V$
V_{FM}	Diode Forward Voltage Drop	1.4	1.7	2.1	V	$I_C = 100A$

Switching Characteristic @ $T_j = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameters	Min	Typ	Max	Unit	Test conditions
C_{ies}	Input capacitance	-	8653	-	pF	$V_{CC} = 25V, V_{GE} = 0V$ $f = 1.0MHz$
C_{oss}	Output capacitance	-	452	-		
C_{res}	Reverse transfer capacitance	-	395	-		
$t_{d(on)}$	Turn-on delay time	-	342	-	ns	$T_j = 125^\circ\text{C}, V_{CC} = 600V$ $I_C = 100A, V_{GE} = \pm 15V$ $R_G = 3.9\Omega$
t_r	Rise time	-	45	-		
$t_{d(off)}$	Turn-off delay time	-	624	-		
t_f	Fall time	-	108	-		
I_{rr}	Diode Peak Reverse Recovery current	-	155	-	A	$T_j = 125^\circ\text{C}, V_{CC} = 600V$ $I_F = 100A,$ $R_G = 3.9\Omega, di/dt = 1200A/\mu s$
t_{rr}	Diode Reverse Recovery time	-	100	-	ns	

Thermal Characteristic Values

Symbol	Parameters	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction-to-Case (IGBT Part, Per 1/2 Module)	-	-	0.20	$^\circ\text{C}/W$
$R_{\theta JC}$	Junction-to-Case (Diode Part, Per 1/2 Module)	-	-	0.41	
$R_{\theta CS}$	Case-to-Heat Sink (Conductive grease applied)	-	0.05	-	

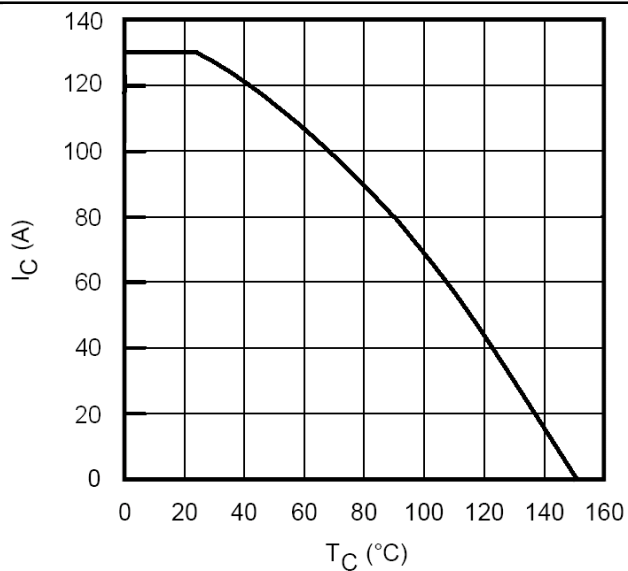


**Fig 1. Maximum DC Collector Current
vs. Case Temperature**

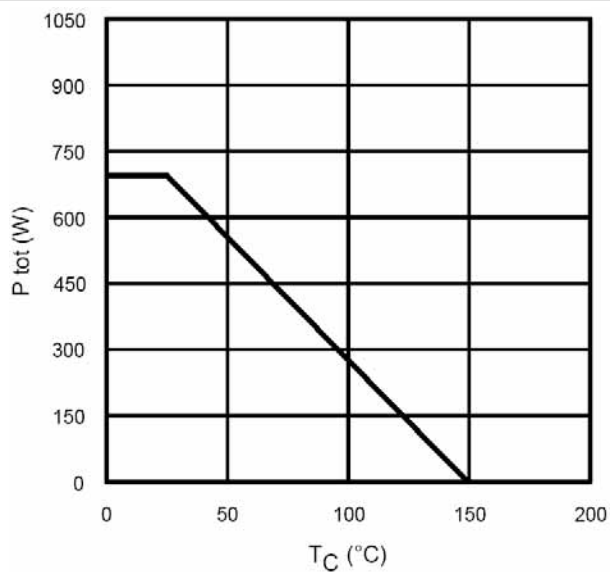


**Fig 2. Power Dissipation vs. Case
Temperature**

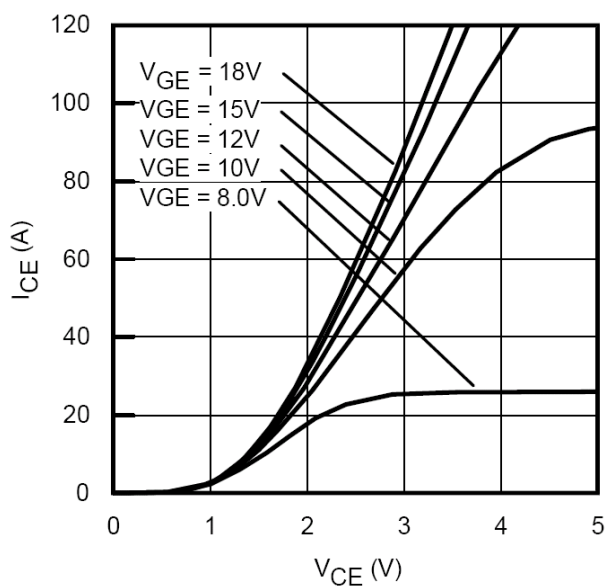


Fig 3. Typ. IGBT Output Characteristics
 $T_J = 25^{\circ}\text{C}$; $t_p = 80\mu\text{s}$

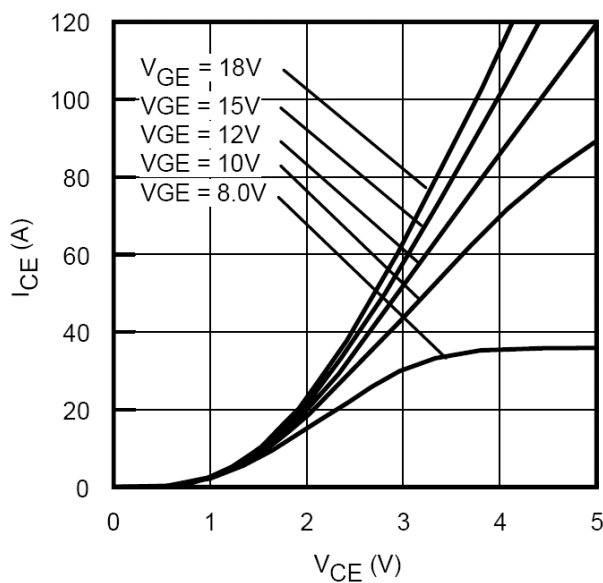


Fig 4. Typ. IGBT Output Characteristics
 $T_J = 125^{\circ}\text{C}$; $t_p = 80\mu\text{s}$

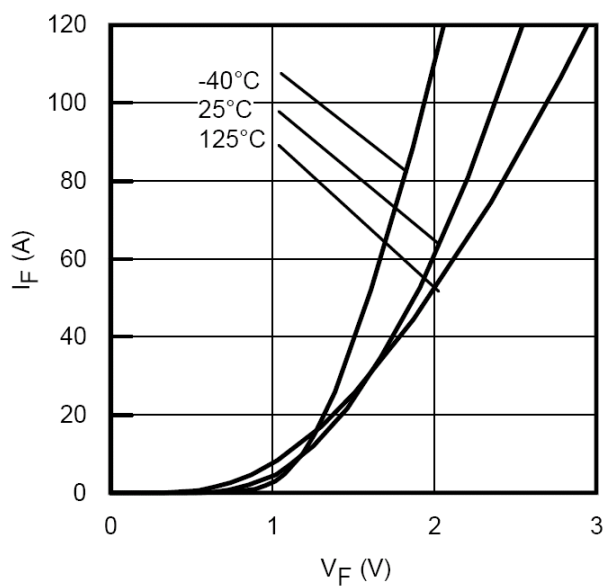


Fig 5. Typ. Diode Forward Characteristics

$t_p = 80\mu s$

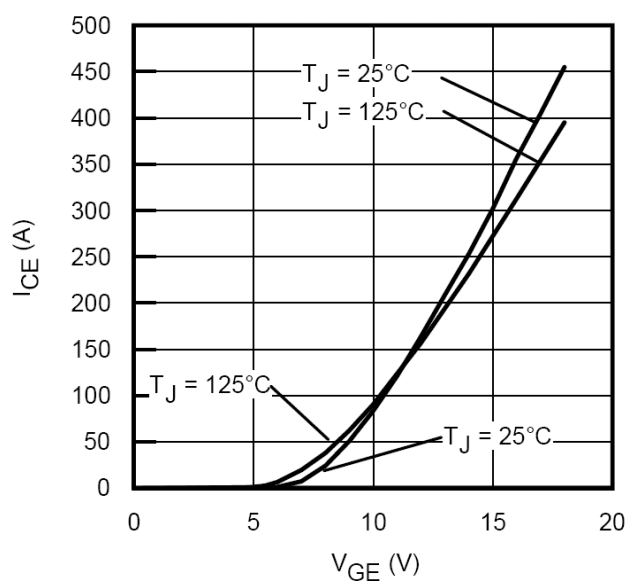


Fig 6. Typ. Transfer Characteristics

$V_{CE} = 50V$; $t_p = 10\mu s$

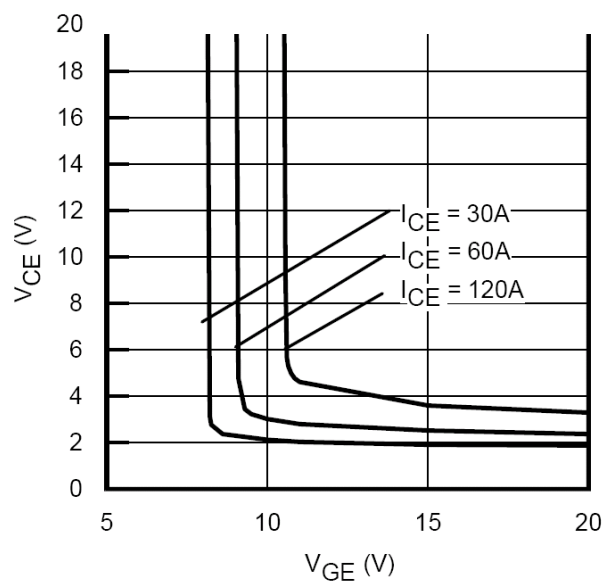


Fig 7. Typical V_{CE} vs. V_{GE}

$T_J = 25^\circ C$

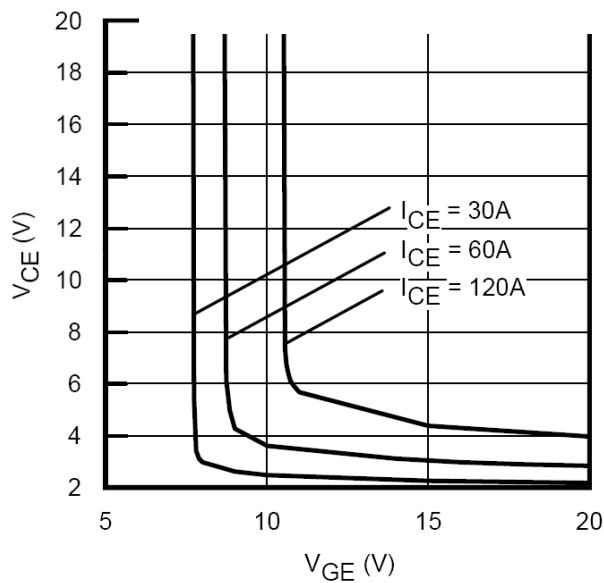


Fig 8. Typical V_{CE} vs. V_{GE}

$T_J = 125^\circ C$

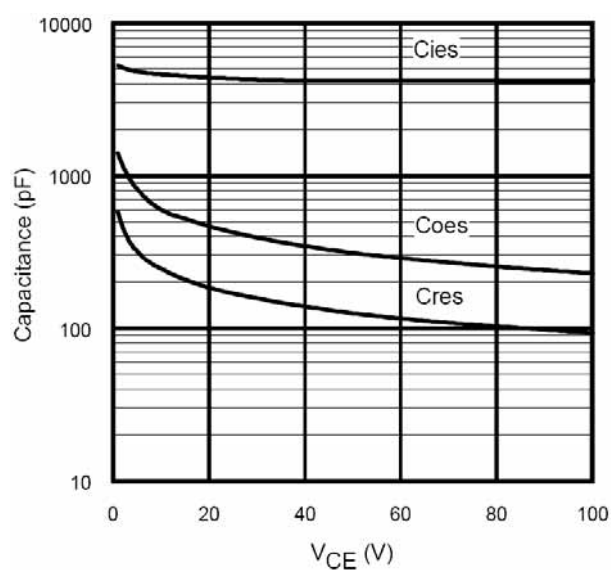


Fig 9. Typ. Capacitance vs. Vce

$V_{GE} = 0V$; $f = 1MHz$

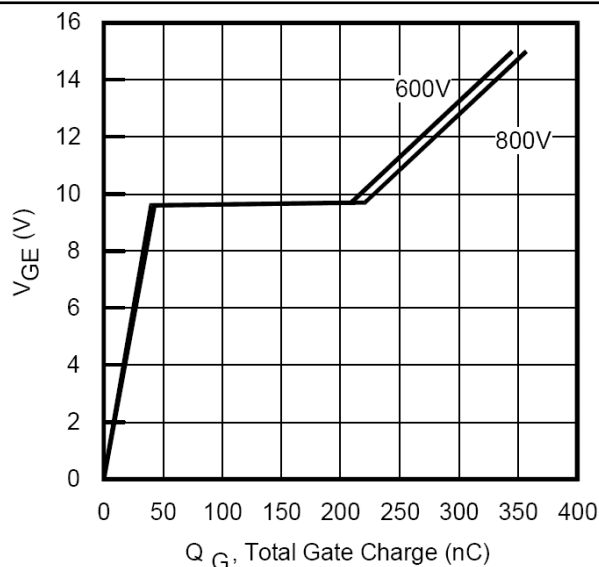


Fig 10. Typical Gate Charge vs. Vge

$I_{CE} = 60A$; $L = 600\mu H$

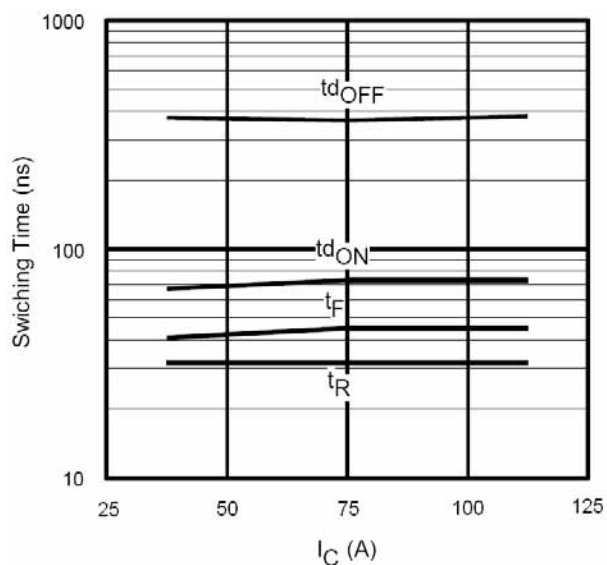


Fig 11. Typ. Switching Time vs. Ic

$T_J = 125^\circ C$; $L = 200\mu H$; $V_{CE} = 600V$

$R_G = 3.9\Omega$; $V_{GE} = 15V$

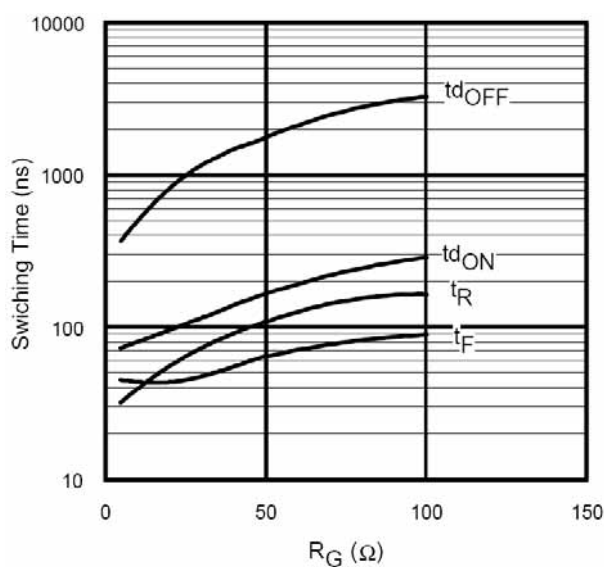


Fig 12. Typ. Switching Time vs. Rg

$T_J = 125^\circ C$; $L = 200\mu H$; $V_{CE} = 600V$

$I_{CE} = 100A$; $V_{GE} = 15V$

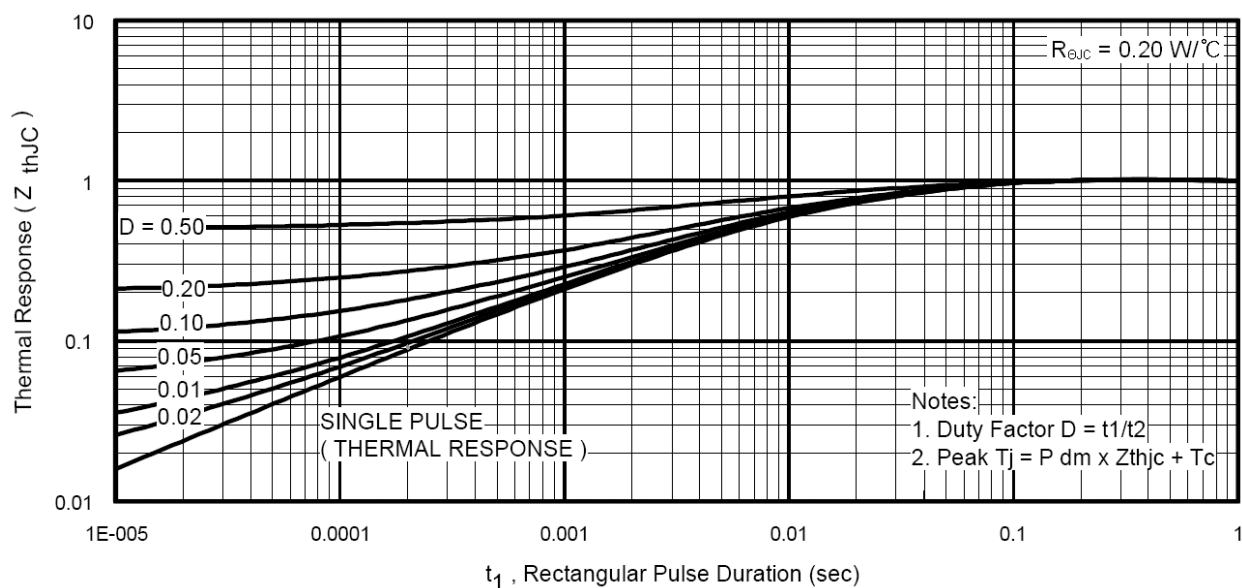


Fig 13. Normalized Transient Thermal Impedance, Junction-to-Case (IGBT)

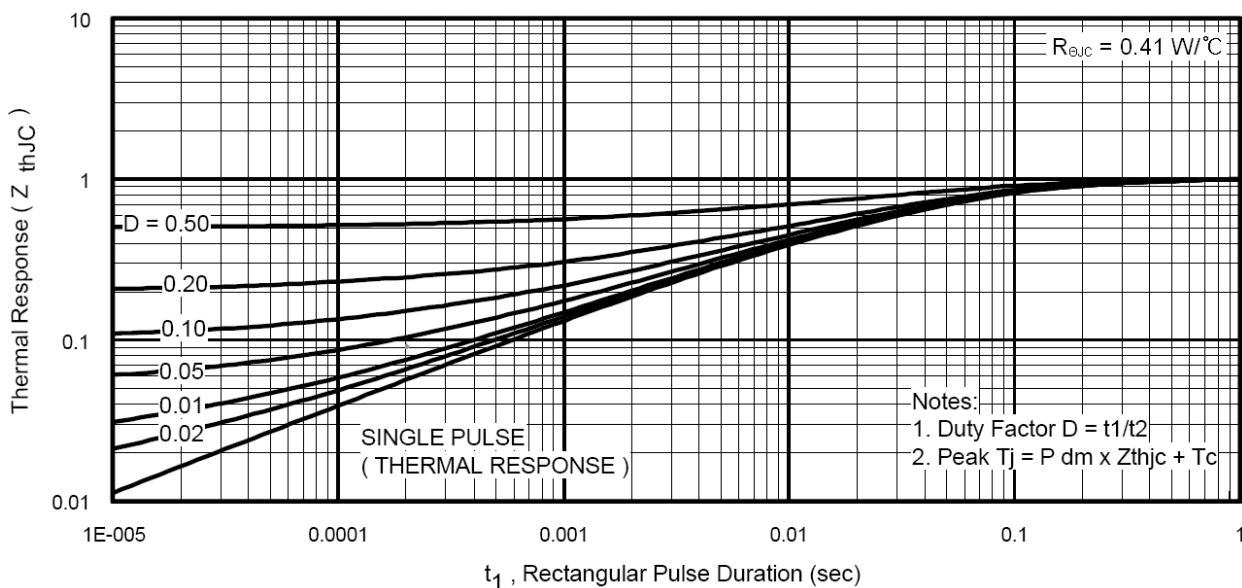
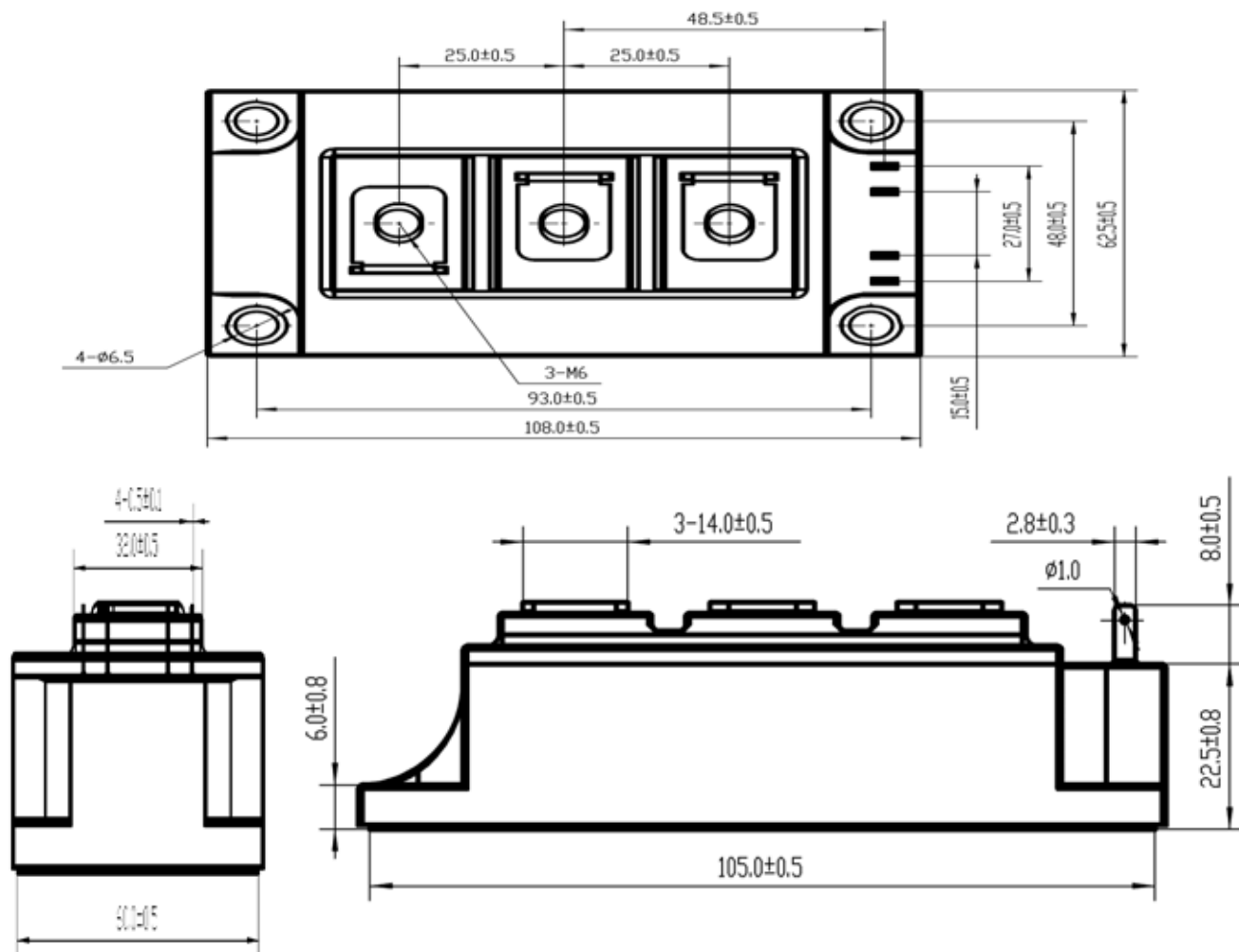


Fig 14. Normalized Transient Thermal Impedance, Junction-to-Case (DIODE)

Package Outline (dimensions in mm)



OCT., 2008

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